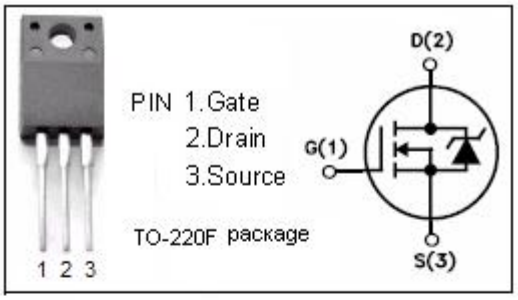
isc N-Channel MOSFET Transistor 2SK1913

DESCRIPTION

- Drain Current –I_D= 4A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=600V(Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

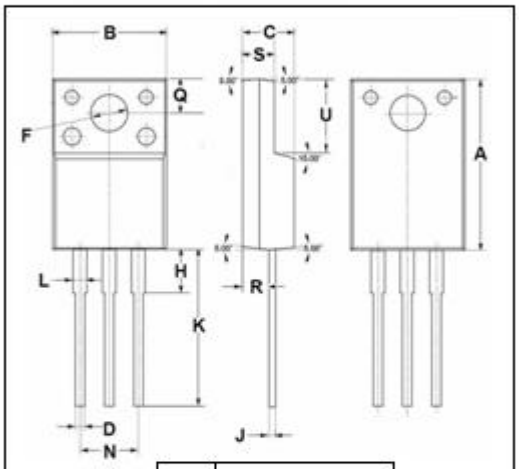
- High speed ,high current switching

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	4	A
P_{tot}	Total Dissipation@TC=25℃	40	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	3.125	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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• ELECTRICAL CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D=250μA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D=1mA	2.1		4	V
V_{DF}	Body to drain diode forward voltage	I_F = 4 A, V_{GS} = 0		0.92	1.41	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 2.5A		0.9	1.8	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V; V_{GS}= 0			100	μA
Ciss	Input capacitance	V_{DS}=25V;V_{GS}=0V;f_T=1MHz		880	1400	pF
Crss	Reverse transfer capacitance			40	60	
Coss	Output capacitance			130	200	
tr	Rise time	V_{GS}=10V;I_D=2.5A; V_{DD}=200V; R_L=80 Ω		25	18	ns
ton	Turn-on time			40	6	
tf	Fall time			45	30	
toff	Turn-off time			130	40	